

tungsten, copper (electroplated or electroless), aluminum, polysilicon, or the like.

39. The structure of claim 29 wherein said passivation layer comprises a layer within the range of approximately 0.15 to 2.0 um Plasma Enhanced CVD (PECVD) oxide over which a layer within the range of approximately 0.5 to 2.0 um PECVD nitride is deposited.

40. The method of claim 29 wherein said insulating, separating layer is a polymer dielectric layer or any other appropriate insulating material.

41. The method of claim 29 wherein said insulating, separating layer comprises polyimide.

42. The method of claim 29 wherein said insulating, separating layer comprises the polymer benzocyclobutene (BCB).

43. The structure of claim 29 wherein said insulating layer is of a thickness after curing within the range of approximately 1.0 to 30 um.

44. The structure of claim 29 wherein said openings have an aspect ratio within the range of approximately 1 to 10.

45. The method of claim 29 wherein said metal conductors within said openings through said insulating layer and through said passivation layer connecting said electrical contact pads of said top metalization structure with contact points of said interconnecting metalization structure are constructed and routed such that each said electrical contact point of said interconnecting metalization structure is connected directly and sequentially with one electrical contact point of said top metalization structure thereby creating a fan-out effect for said electrical contact point of said interconnecting metalization structure whereby the distance between said electrical contact points of said top metalization structure is larger than the distance between said electrical contact points of said interconnecting metalization structure by a measurable amount.

46. The method of claim 29 wherein said the number of said electrical contact pads of said upper metalization structure can be larger than the number of said contact points of said interconnecting metalization structure by a considerable and measurable amount.

47. The method of claim 29 wherein said metal conductors within said openings through said insulating layer and through said passivation layer connecting said electrical contact points of said top metalization structure with said contact points of said interconnecting metalization structure are constructed and routed such that each said electrical contact point of said interconnecting metalization structure is connected directly but not necessarily sequentially with one electrical contact point of said top metalization structure thereby creating a pad relocation effect for said electrical contact points of said interconnecting metalization structure whereby the distance between said electrical contact points of said top metalization structure is larger than the distance between said electrical contact point of said interconnecting metalization structure by a measurable amount whereby furthermore the sequence or adjacency of said electrical contact points of said interconnecting metalization structure is not necessarily the same as the sequence or adjacency between said electrical contact points of said top metalization structure.

48. The method of claim 29 wherein said metal conductors within said openings through said insulating layer and through said passivation layer connecting said electrical contact points on a top surface of said top metalization structure with contact